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# ELECTROSTATIC DISCHARGE PROTECTION CIRCUIT OF NON-GATED DIODE AND FABRICATION METHOD THEREOF

## CROSS-REFERENCE TO RELATED APPLICATION

5           This application claims the priority benefit of Taiwan application serial no. 91101026, filed January 23, 2002.

## BACKGROUND OF THE INVENTION

### Field of the Invention

10           [0001] The invention relates in general to an electrostatic discharge protection circuit and a fabrication method thereof, and more particularly, to an electrostatic discharge protection circuit of a non-gated diode and a fabrication method thereof that uses the silicon-on-insulation (SOI) fabrication process.

### Description of the Related Art

15           [0002] Silicon-on-insulator technology is a prime contender for low voltage, and high-speed applications because of its advantages over bulk-Si technology in high isolation, latch-up immunity, and smaller junction capacitance. However, electrostatic discharge (ESD) is a major concern for SOI technology.

20           [0003] The protection level provided by an ESD protection circuit is determined by the amount of current that it can sink while clamping the voltage to a small value. The device failure is initiated by thermal runaway and followed by catastrophic damage during an ESD pulse. In SOI devices, the presence of the buried oxide layer having a thermal conductivity  $1/100^{\text{th}}$  of Si causes increased device heating, which in turn accelerates thermal runaway under ESD stress condition.

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[0004] Figure 1 depicts a cross-sectional view of a gated-diode (called as Lubistor) in SOI published in the article of S. Voldman et al. "CMOS-on-SOI ESD protection networks," in *Proc. Of EOS/ESD Symp.* 1996, pp. 291-301. As shown in Figure 1, the SOI gated diode is formed on a SOI substrate which includes a substrate 10, a buried oxide layer 12 and a silicon layer. Shallow trench isolation (STI) structures 14 are formed in the silicon layer. A P+ region 20 and an N+ region 16 are formed in the silicon layer between the STI structures 14, while a N-type or P-type doped region 18 is formed in the silicon layer between the P+ region 20 and the N+ region 16. If the N-type doped region 18 is selected, the P+ region 20 and the N- doped region 18 construct a SOI diode. In contrast, if the P-type doped region 18 is formed, the N+ region 16 and the P-type doped region 18 construct a SOI diode. A gate is further formed on the doped region 18. The gate includes a P+ region 24 and an N+ region, a spacer 26 and a gate oxide 28.

[0005] The P+ region 20 and the N+ region 16 are coupled to voltage V1 and V2 as the voltage application terminals for the SOI diode. Taking the SOI diode formed of the P+ region 20 and the N-type doped region 18 as an example, the SOI diode is forward biased if V1 is positive relative to V2. On the contrary, if V2 is positive relative to V1, the SOI diode is reverse biased.

[0006] If the heat generated by the ESD voltage at the junction between the P+ region 20 and the N-type doped region 18 is small, the SOI diode can withstand a higher ESD voltage. The heat generated at the PN junction is joule heating. When the maximum temperature of the SOI diode reaches its intrinsic temperature,  $T_{intrinsic}$ , second order breakdown occurs. Therefore, to obtain a better ESD protection, the power density and joule heating have to be reduced in the device structure.

## SUMMARY OF THE INVENTION

[0007] The invention provides an ESD protection circuit of a non-gated diode and a fabrication method thereof. The non-gated diode has low power density.

[0008] The ESD protection circuit of a non-gated diode and the fabrication  
5 method thereof can be applied to a SOI circuit, so as to enhance the voltage withstanding effect.

[0009] Another objective of the invention is to provide an ESD protection circuit of a non-gated diode and the fabrication method thereof applicable to SOI fabrication process or the bulk CMOS fabrication process.

10 [0010] To achieve the above characteristics and objectives, the invention provides an ESD protection circuit of a non-gated diode structure, and a fabrication method thereof as described as follows.

[0011] A non-gated diode structure of a silicon on insulator is provided. The silicon on insulator includes a substrate, an insulator layer and a silicon layer  
15 sequentially stacked together. A pair of isolating structures is located in the silicon layer to define a well region. A first type doped region and a second type doped region are located in the well region and are respectively adjacent to the isolating structures.

[0012] The invention further provides a non-gated diode structure of a silicon on insulator. The silicon on insulator includes a substrate, an insulator layer and a silicon  
20 layer stacked in sequence. A pair of isolating structures is formed in the silicon layer. A first well region and a second well region adjacent to each other are formed in the silicon layer between the isolating structures. A first doped region and a second doped region are respectively formed in the first well region and the second well region and

are adjacent to the isolating structures. The junction of the non-gated diode of the silicon on insulator is thus the junction between the first and the second well regions.

[0013] An ESD protection circuit of a non-gated diode coupled between input pads and internal circuit is further provided in the invention. The ESD protection circuit  
5 comprises a Vdd voltage supply rail, a Vss voltage supply rail, a first diode, a second diode, a first diode series, a second diode series and an input resistor. The first diode has an anode coupled to the Vdd voltage supply rail and a cathode coupled to a node. The second diode has a cathode coupled to the Vss voltage supply rail and an anode coupled to the node. The first diode series comprises a plurality of serially connected  
10 diodes with an anode coupled to the Vdd voltage supply rail and a cathode coupled to the node. The second diode series comprises a plurality of serially connected diodes with a cathode coupled to the Vss voltage supply rail and an anode coupled to the node. The input resistor has a first end coupled to the node and a second end coupled to the internal circuit.

15 [0014] When a voltage positive relative to the Vdd voltage supply rail is applied to the input pads, the ESD protection circuit of the non-gated diode provides a discharge path from the first diode to the high-voltage supplying line. When a voltage negative relative to the Vss voltage supply rail is applied to the input pads, the ESD device of the non-gated diode provides a discharge path from the second diode to the Vss voltage  
20 supply rail. When a voltage negative relative to the Vdd voltage supply rail is applied to the input pads, the ESD protection circuit of the non-gated diode provides a discharge path through the second diode, the second diode series and the first diode series to the high-voltage supplying line. When a voltage positive relative to the Vss voltage supply rail is applied to the input pads, the ESD device of the non-gated diode provides a

discharge path through the first diode, the first diode series, and the second diode series to the Vss voltage supply rail.

[0015] An ESD protection circuit is further provided and coupled between an output pad and a pre-driver. The ESD protection circuit comprises a Vdd voltage supply rail, a Vss voltage supply rail, a first diode, a second diode, a first diode series, a second diode series, a first type MOS transistor and a second type MOS transistor. The Vdd voltage supply rail and the Vss voltage supply rail are coupled to the pre-driver. The first diode has an anode coupled to the Vdd voltage supply rail and a cathode coupled to a node. The second diode has a cathode coupled to the Vss voltage supply rail and an anode coupled to the node. The first diode series comprises a plurality of serially connected diodes, of which an anode is coupled to the Vdd voltage supply rail and a cathode is coupled to the node. The second diode series comprises a plurality of serially connected diodes with a cathode coupled to the Vss voltage supply rail and an anode coupled to the node. The first type has a source region coupled to the Vdd voltage supply rail, a drain region coupled to the node and a gate coupled to the pre-driver. The second type MOS transistor has a source region coupled to the Vss voltage supply rail, a drain region coupled to the node and a gate coupled to the gate of the first type MOS transistor.

[0016] In the above ESD protection circuit, when a voltage positive relative to the high voltage supply line is applied to the output pad, a discharge path is provided through the first diode to the Vdd voltage supply rail. When a voltage negative relative to the Vss voltage supply rail is applied to the output pad, a discharge path is provided through the second diode to the Vss voltage supply rail. When a voltage negative relative to the Vdd voltage supply rail is applied to the output pad, a discharge path is

provided through the second diode, the second diode series, the first diode series and the high-voltage discharge line. When a voltage positive relative to the Vss voltage supply rail is applied to the output pad, a discharge path through the first diode, the first diode series and the second diode series to the Vss voltage supply rail is provided.

5           **[0017]** In another embodiment of the invention, an ESD protection circuit of a non-gated diode is provided and coupled between an input pad and an internal circuit. The protection circuit comprises the following devices. A Vdd voltage supply rail and a low-voltage supply are coupled to the internal circuit. A first diode and a second diode are serially connected to each other. The anode of the first diode is coupled to a node,  
10 while the cathode of the second diode is coupled to the Vdd voltage supply rail. A third diode and a fourth diode are serially connected to each other. The anode of the third diode is coupled to the Vss voltage supply rail, while the cathode of the fourth diode is coupled to the node. An input resistor has a first terminal coupled to the node and a second terminal coupled to the internal circuit. A MOS transistor has a gate and a  
15 source region connected to the Vss voltage supply rail, and a drain region coupled to the second terminal of the ballast resistor. An ESD clamp circuit is coupled between the high-and low- voltage supply lines.

**[0018]** The above discharge clamp circuit comprises a plurality of diodes serially connected together with an anode coupled to the Vdd voltage supply rail and a  
20 cathode coupled to the Vss voltage supply rail.

**[0019]** The invention further provides a method for forming a non-gated diode on a SOI. A SOI comprising a substrate, an insulation layer and a silicon layer are provided. A pair of isolating structures is formed in the silicon layer to define a well

region. A first type doped region and a second doped region are formed in the well region and respectively adjacent to one of the isolating structures.

[0020] The invention further provides another method for forming a non-gated diode on a SOI. A SOI comprising a substrate, an insulation layer and a silicon layer are provided. A pair of isolating structures is formed in the silicon layer. A first well region and a second well region are formed in the silicon layer between the isolating structures, and the first and second well regions are adjacent to each other. A first type doped region and a second doped region are formed in the first and second well regions, respectively. Thereby, the junction of the non-gated diode of the SOI is the junction between the first and second well regions.

[0021] The invention further provides a non-gated diode structure of a CMOS, comprising: a substrate having a well region therein; a pair of blocking isolation structures in the substrate; a first type doped region located in the well region and between the blocking isolation structures; and a pair of second type doped regions located in the well region and respectively adjacent to the blocking isolation structure, wherein each second type doped region is separated from the first type doped region by the well.

[0022] The invention further provides a method of forming a non-gate diode of a CMOS, comprising: providing a substrate having a well region therein; forming a pair of blocking isolation structures in the substrate; forming a first type doped region located in the well region and between the blocking isolation structures; and forming a pair of second type doped regions located in the well region and respectively adjacent to the blocking isolation structure, wherein each second type doped region is separated from the first type doped region by the well.

[0023] Both the foregoing general description and the following detailed description are exemplary and explanatory only and are not restrictive of the invention, as claimed.

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## BRIEF DESCRIPTION OF THE DRAWINGS

[0024] Figure 1 shows a cross sectional view of a gated diode of a SOI, such as an ESD protection circuit of CMOS of a SOI;

[0025] Figure 2 shows a cross sectional view of a non-gated diode with a STI-blocking structure in one embodiment of the invention;

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[0026] Figure 3A to Figure 3B show the top views of the STI-isolating structures and the STI-blocking structure;

[0027] Figure 4A to Figure 4G show the fabrication process of STI-isolating structure using SOI fabrication process;

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[0028] Figure 5A to Figure 5G show the fabrication process of STI-blocking structure using SOI fabrication process;

[0029] Figure 6A to Figure 6G show the fabrication process of STI-isolating structure using bulk CMOS fabrication process;

[0030] Figure 7A to Figure 7G show the fabrication process of STI-blocking structure using bulk CMOS fabrication process;

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[0031] Figure 8 shows a comparison of Human-Body-Model (HBM) ESD level between the gated diode and the non-gated diode;

[0032] Figure 9 shows a cross sectional view of a non-gated diode with a STI-blocking structure in another embodiment of the invention.



[0033] Figure 10 illustrates the input ESD protection circuit of the SOI non-gated diode.

[0034] Figure 11 illustrates the output ESD protection circuit of the SOI non-gated diode.

5 [0035] Figure 12 illustrates another input ESD protection circuit of the SOI non-gated diode with power-rail ESD clamp.

[0036] Figure 13 illustrates another ESD protection circuit of the SOI non-gated diode with the power-rail ESD clamp realized by the non-gated diodes.

## 10 DESCRIPTION OF THE PREFERRED EMBODIMENTS

[0037] Figure 2 is a cross-sectional view showing an embodiment of a non-gated diode with a STI-blocking structure. In Figure 2, the SOI non-gated diode is formed on a SOI substrate that includes a substrate 40, an insulation layer 42 and a silicon layer. The substrate 40 includes either a P-type substrate or an N-type substrate. The insulation layer 42 includes a buried oxide layer. The SOI non-gated diode with the STI blocking structure is formed in the silicon layer. In the silicon layer, the SOI non-gated diode is formed between two STI blocking structures 44. That is, the doped region of the SOI non-gated diode is isolated by the two STI structures. A lightly doped well region 50 doped with P-type or N-type ions (P-well or N-well) is formed on the insulation layer 42 between the two STI structures. In addition, heavily doped P-type (P+) diffusion region 48 and heavily doped N-type (N+) diffusion region 46 are formed in the corners of the P- or N-well region 50 adjacent to the two STI structures 44.

[0038] The STI structures formed in the SOI fabrication process include STI-isolating structure and STI-blocking structure. Figures 3A and 3B respectively show

the top views of these two structures. In the following description, it will be seen that the STI-isolating structure cannot form the SOI diode since each doped region is fully isolated by the STI structure. In Figure 3A, a plurality of STI structures 60 is formed in the silicon layer on the insulation layer 62. The doped regions 64 (N+), 66 (P+) and 68 (N+) are formed between the STI structures 60 and unconnected to each other. Therefore, a P-N junction of the diode cannot be formed. In Figure 3B, the STI structures 70 are formed in the silicon layer on the insulation layer 72, while the doped regions 74 (N+), 76 (P+) and 78 (N+) are formed between two STI structures 70. A P-N junction of a diode can thus be formed.

[0039] Figures 4A to 4G illustrate the STI-isolating structure fabricated using SOI process, while Figures 5A to 5G illustrate the STI-blocking structure fabricated using SOI process. From the results, it is shown that the doped regions formed in the process for the STI-isolating structure are not connected to each other, so that a P-N junction of the diode cannot be formed.

[0040] Referring to figures 4A and 5A, substrates 100a, 100b are provided. Insulating layers 102a, 102b are formed on the substrates 100a, 100b, respectively. A silicon layer is formed on the insulating layers 102a and 102b. The insulating layers 102a, 102b include buried oxide layer. In addition, P-type ion is implanted into the silicon layer to form P-well regions 104a, 104b. Thus far, the process steps are similar.

[0041] Figures 4B and 4C, a pad oxide layer 106b and a photoresist layer 108b are formed with the region for forming the STI structure exposed. Using the pad oxide layer 106b and the photoresist layer 108b as a mask, the P-well region (silicon layer) 104b is etched to form a trench. The pad oxide layer 106b and the photoresist layer 108b are removed. An insulating material is filled into the trench, followed by a

planarization step to form a STI structure.

[0042] Referring to Figure 4D, a photoresist layer 112b is formed on a part of the P-well region 104b and a part of the STI structure 110b, while the P-well region 104b encircled by the STI structure is exposed. An ion implantation step is performed to implant P-type ions into the exposed P-well region 104b, so as to form a P+ region 114b. In Figure 4E, the photoresist layer 112b is removed. In Figure 4F, a photoresist layer 116b is formed on the P+ region 114b, and an ion implantation step is performed. N-type ion is implanted into the exposed P-well region to form N+ region 118b. The photoresist layer 116b is removed as shown in Figure 4G.

[0043] Referring to Figures 5B and 5C, a pad oxide layer 106a and a photoresist layer 108a are formed, while the region for forming the STI structure is exposed. Using the pad oxide layer 106a and the photoresist layer 108a as a mask, the P-well region 104a is etched to form a trench. The pad oxide layer 106a and the photoresist layer 108a are removed. An insulating material is filled into the trench, followed by a planarization step to form the STI structure. Referring to Figure 5D, a photoresist layer 112a is formed on a part of the P-well region 104a and a part of the STI structure 110a, while a part of the P-well region 104a is exposed. An ion implantation step is performed to implant P-type ion into the exposed P-well region 104a, so that a P+ region 114a is formed. In Figure 5E, the photoresist layer 112a is removed. In Figure 5F, a photoresist layer 116a is formed in the P+ region 114a, and an ion implantation step is performed. The width of the photoresist layer 116a is slightly larger than the underlying P+ region 114a. N-type ion is implanted into the P-well region 104a to form the N+ region 118a. The photoresist layer 116a is removed. In Figure 5G, as the width of the photoresist layer 116a is slightly larger than the underlying P+ region 114a, a P-

well region 120 is formed between the N+ region 118a and the P+ region 114a with a width SP.

[0044] The key parameters of the non-gated STI-blocking diode of the SOI CMOS fabrication process used for ESD protection are diode dimension, well doping concentration, and the spacing SP between the cathode node and the anode node of the diode. The spacing SP not only affects the on-resistance of the diode in ESD discharging under forward biased, but also affects the reverse breakdown voltage of the diode. Therefore, by properly controlling the spacing SP, any proper reverse breakdown voltage of the ESD protection circuit can be fabricated.

[0045] Figures 6A to 6G show using bulk CMOS process to form the STI-isolating structure, while Figures 7A to 7G show using bulk CMOS process to form the STI-blocking structure.

[0046] Referring to Figures 6A and 7A, substrates 200a, 200b are provided. P-well regions 202a, 202b are formed in the substrates 200a, 200b, respectively. Thus far, the process steps are similar.

[0047] Referring to Figures 6B and 6C, a pad oxide layer 204b and a photoresist layer 206b are formed with the region for forming STI structure exposed. Using the pad oxide layer 204b and the photoresist layer 206b as a mask, the P-well region 202b is etched to form a trench. The pad oxide layer 204b and the photoresist layer 206b are removed. An insulating material is filled into the trench, followed by a planarization step to form a STI structure. Referring to Figure 6D, a photoresist layer 210b is formed on a part of the P-well region 202b and a part of the STI structure 208b, while the P-well region 202b encircled by the STI structure is exposed. An ion implantation step is performed to implant P-type ions into the exposed P-well region 202b, so as to form a

P+ diffusion region 212b. In Figure 6E, the photoresist layer 210b is removed. In Figure 6F, a photoresist layer 214b is formed on the P+ diffusion region 212b, and an ion implantation step is performed. N-type ion is implanted into the exposed P-well region 202b to form an N+ diffusion region 216b. The photoresist layer 214b is removed as shown in Figure 6G.

[0048] Referring to Figures 7B and 7C, a pad oxide layer 204a and a photoresist layer 206a are formed, while the region for forming the STI structure is exposed. Using the pad oxide layer 204a and the photoresist layer 206a as a mask, the P-well region 202a is etched to form a trench. The pad oxide layer 204a and the photoresist layer 206a are removed. An insulating material is filled into the trench, followed by a planarization step to form the STI structure. Referring to Figure 7D, a photoresist layer 210a is formed on a part of the P-well region 202a and a part of the STI structure 208a, while a part of the P-well region 202a is exposed. An ion implantation step is performed to implant P-type ion into the exposed P-well region 202a, so that a P+ region 212a is formed. In Figure 7E, the photoresist layer 210a is removed. In Figure 7F, a photoresist layer 214a is formed in the P+ region 212a, and an ion implantation step is performed. The width of the photoresist layer 214a is slightly larger than the underlying P+ region 212a. N-type ion is implanted into the P-well region 202a to form N+ region 216a. The photoresist layer 214a is removed. In Figure 7G, as the width of the photoresist layer 214a is slightly larger than the underlying P+ region 212a, a P-well region 218 is formed between the N+ region 216a and the P+ region 212a with a width SP.

[0049] According to the above, from the comparison between Figure 6G and Figure 7G, it can be seen that only the process with STI-blocking structure can form a

diode with adjacent lateral P-N junction.

[0050] The key parameters of the non-gated STI-blocking diode of the bulk CMOS fabrication process used for ESD protection include diode dimension, the well doping concentration, and the spacing SP between the cathode node and the anode node of the diode. The spacing SP not only affects the on-resistance when the diode is forward biased, but also affects the reverse breakdown voltage. Therefore, by properly controlling the spacing SP, any suitable reverse breakdown voltage of the ESD protection circuit can be fabricated.

[0051] Figure 8 shows the experimental results between the perimeters of the gated and non-gated diode and the ESD voltage. Conclusions as follows can be made.

1. As the diodes becomes wider and wider, the ESD voltage that the device can withstand is greater and larger, so that the internal circuit can be further protected.
2. The ESD voltage that the non-gated SOI diode can withstand is greater than that the gated diode can withstand. As the ESD robustness and the diode perimeters shows a linear relationship, the invention can use the non-gated diode in SOI process or bulk CMOS process to estimate and design the ESD level of an ESD protection circuit.

[0052] Figure 9 shows another embodiment of a non-gated STI-blocking diode. In Figure 9, the SOI non-gated diode is formed on a SOI substrate that comprises a substrate 90, an insulating layer 92 and a silicon layer. The substrate 90 includes a P- or an N- substrate, while the insulating layer includes a buried oxide layer. The SOI non-gated STI-blocking diode is formed in the silicon layer. In the silicon layer, the SOI diode is formed between two STI structures 94. That is, the doped regions of the SOI diode are isolated by two STI structures. On the insulating layer 92 and between the STI structures, two neighboring lightly doped P-type and N-type doped regions (P- well

and N- well regions) are formed. In addition, heavily doped P+ diffusion region 96b and N+ diffusion region 96a are formed between the STI structures 94 and the P- well region and N- well region 98b, 98a. The difference between this embodiment and Figure 2 includes that the PN junction of the SOI non-gated diode is located in the middle of the whole structure, while the PN junction in Figure 2 is located at the edge.

[0053] Several examples are used to describe the application of the ESD protection circuit of SOI non-gated diode provided by the invention.

[0054] Figure 10 illustrates the application of the SOI non-gated diode in Figure 2 or Figure 9 in the input ESD protection circuit. The ESD protection circuit includes an input pad 300, a first diode D1, a second diode D2, a first diode series 302, a second diode series 304, an input resistor R, and a Vdd voltage (high-voltage) supply rail and a Vss voltage (low-voltage) supply rail. An internal circuit 306 is connected between the Vdd voltage supply rail, the Vss voltage supply rail and the input resistor R. The first diode D1 has a cathode coupled to Vdd and an anode coupled to the pad 300. The second diode D2 has an anode coupled to Vss, and a cathode coupled to the pad 300. The first diode series 302 includes a plurality of diodes Du1, Du2, ..., Dun with the anodes and cathodes serially connected to each other. The anode of the diode Du1 is coupled to Vdd, and the cathode of the diode Dun is coupled to the pad 300. The second diode series 304 includes a plurality of diodes Dd1, Dd2, ..., Ddn with the anodes and cathodes serially connected to each other. The anode of the diode Dd1 is coupled to the pad 300, and the cathode of the diode Ddn is coupled to Vss. Each diode of the first diode D1, the second diode D2, the first diode series 302 and the second diode series 304 includes the SOI non-gated diode as shown in Figure 2 or Figure 9. In addition, the input resistor R can be connected to an input buffer (not shown) of the

internal circuit 306.

[0055] Figure 10 illustrates the operation method of the input ESD protection circuit. When an ESD event with a voltage positive relative to the Vdd voltage supply rail is applied to the input pad 300, the first diode D1 is forward biased. As the Vss voltage supply rail is floating, the second diode D2 is not effective. Therefore, the ESD event (voltage) is discharged from the first diode D1 to the Vdd voltage supply rail. Similarly, when an ESD event with a voltage negative relative to the Vss voltage supply rail is applied to the input pad 300, the second diode D2 is forward biased. As the Vdd voltage supply rail is floating, the first diode D1 is ineffective. Therefore, the ESD event (voltage) is discharged from the second diode D2 to the Vss voltage supply rail.

[0056] When an ESD event with a voltage negative relative to the Vdd voltage supply rail is applied to the input pad 300, the first diode D1 is reverse biased. As the Vss voltage supply rail is floating, the voltage Vss will follow up to the input pad 300 with a negative voltage. Meanwhile, the first diode series 302 (Du1, Du2, ..., Dun) are forward biased, so that the negative ESD discharge current flows from the first diode series 302 (Du1, Du2, ..., Dun) to Vdd.

[0057] When an ESD event with a voltage positive relative to the Vss voltage supply rail is applied to the input pad 300, the second diode D2 is reverse biased. As the Vdd voltage supply rail is floating, the voltage Vdd will follow up to the input pad 300 with a positive voltage. Meanwhile, the second diode series 304 (Dd1, Dd2, ..., Ddn) are forward biased, the ESD discharge current flows from the second diode series 304 (Dd1, Dd2, ..., Ddn) to Vss.

[0058] Figure 11 illustrates the output ESD protection circuit with the SOI non-gated diode as shown in Figure 2 or Figure 9. As shown in Figure 11, the ESD



protection includes an output pad 310, a first diode D1, a second diode D2, a first diode series 312, a second diode series 314, a PMOS transistor Mp, an NMOS transistor Mn, a Vdd voltage supply rail and a Vss voltage supply rail. A pre-driver 316 is coupled between the Vdd and Vss voltage supply rails, the PMOS transistor Mp and the NMOS transistor Mn. The first diode D1 has a cathode coupled to Vdd and an anode coupled to the pad 310. The second diode D2 has an anode coupled to Vss and a cathode coupled to the pad 310. The first diode series 312 comprises a plurality of diodes Du1, Du2, ..., Dun with anodes and cathodes serially connected to each other. The anode of the diode Du1 is coupled to Vdd, and the cathode of the diode Dun is coupled to the pad 310. The second diode series 314 comprises a plurality of diodes Dd1, Dd2, ..., Ddn with anodes and cathodes serially connected to each other. The anode of the diode Dd1 is coupled to pad 310, and the cathode of the diode Ddn is coupled to Vss. The source region of the PMOS transistor Mp is coupled to Vdd, and the source region of the NMOS transistor Mn is coupled to Vss. The drain regions of the PMOS and NMOS transistors Mp and Mn are coupled to the pad 310. Each of the first diode D1, the second diode D2, the first diode series 312 and the second diode series 314 includes the SOI non-gate diode as illustrated in Figure 2 or Figure 9.

[0059] Figure 11 illustrates the operation method of the output ESD protection circuit. When an ESD event with a voltage positive relative to the Vdd voltage supply rail is applied to the output pad 310, the first diode D1 is forward biased. As the Vss voltage supply rail is floating, the second diode D2 is not active. Therefore, the ESD event (voltage) is discharged to the Vdd voltage supply rail through the first diode D1. Similarly, when an ESD event with a voltage negative relative to the Vss voltage supply rail is applied to the output pad 310, the second diode D2 is forward biased. As the Vdd

voltage supply rail is floating, the first diode D1 is inactive. Therefore, the ESD event (voltage) is discharged to the Vss voltage supply rail through the second diode D2.

[0060] When an ESD event with a voltage negative relative to the Vdd voltage supply rail is applied to the output pad 310, the first diode D1 is reverse biased. As the Vss voltage supply rail is floating, the voltage Vss will follow up to the output pad 310 with a negative voltage. Meanwhile, the first diode series 312 (Du1, Du2, ..., Dun) are forward biased, so that the negative ESD discharge current flows from the first diode series 312 (Du1, Du2, ..., Dun) to Vdd.

[0061] When an ESD event with a voltage positive relative to the Vss voltage supply rail is applied to the output pad 310, the second diode D2 is reverse biased. As the Vdd voltage supply rail is floating, the voltage Vdd will follow up to the output pad 310 with a positive voltage. Meanwhile, the second diode series 314 (Dd1, Dd2, ..., Ddn) are forward biased, the ESD discharge current flows from the second diode series 314 (Dd1, Dd2, ..., Ddn) to Vss.

[0062] Figure 12 illustrates the input ESD protection circuit with the SOI non-gated diode as shown in Figure 2 or Figure 9. As shown in Figure 12, the ESD protection includes an input pad 320, a first diode D1, a second diode D2, a third diode D3, a fourth diode D4, a Vdd voltage supply rail, a Vss voltage supply rail, an NMOS transistor Mn, and an ESD clamp circuit 324. The internal circuit 322 is coupled between the Vdd and Vss voltage supply rails, the input resistor R and the NMOS transistor Mn. The first and second diodes D1 and D2 are serially connected to each other with the anode of the first diode D1 connecting to the input pad 320 and the cathode of the second diode D1 connecting to Vdd. The third diode D3 and the fourth diode D4 are connected to each other in series with the anode of the third diode D3

connecting to Vss, and the cathode of the fourth diode D4 connecting to the input pad 320. The input resistor R has one terminal coupled to the pad 320, and the other terminal coupled to the drain region of the NMOS transistor Mn and the internal circuit 322. The gate and source region of the NMOS transistor are coupled to Vss. The above  
5 diodes D1, D2, D3 and D4 include the SOI non-gated diode as shown in Figure 2 or Figure 9.

[0063] The operation of the circuit in Figure 12 is similar to those in Figure 10 or Figure 11, so that the description thereof is not repeated. As shown in Figure 12, the first and the second diodes D1 and D2 are to replace the diode D1 in Figure 10 or 11,  
10 while the third and fourth diodes D3 and D4 are to replace the diode D2 in Figure 10 or 11. The diodes D1, D2, D3 and D4 have a parasitic junction capacitor C1, C2, C3 and C4, respectively. In Figure 10, the input capacitance Cin is  $C1+C2$ , while in the embodiment as shown in Figure 12, the input capacitance Cin is  $[C1C2/(C1+C2)]+[C3C4/(C3+C4)]$ . If the diodes D1, D2, D3 and D4 are the same,  
15 then  $C1=C2=C3=C4=C$ . Therefore,  $Cin=2C$ , and  $Cin'=C$ . The input capacitance of Figure 12 is reduced, so that the RC time constant is reduced. By reducing the input delay, the ESD protection circuit can be applied to the high frequency (HF) circuits.

[0064] Figure 13 illustrates a modification of Figure 12. A diode series 334 is used to realize the ESD clamp circuit between Vdd and Vss. The diode series 334 is  
20 used as an ESD clamp circuit. The diode series 334 comprises diodes Dp1, Dp2, ..., Dpn such as the SOI non-gated diode in Figure 2 or Figure 9 serially connected together.

[0065] Thus, the invention has the advantages:

[0066] 1. The non-gated diode is compatible to the general SOI COS fabrication process (such as Figure 5A to Figure 5G) and the general bulk CMOS fabrication

process (such as Figure 7A to Figure 7G).

[0067] 2. More PN junction area is obtained compared to gated diode, so that the SOI non-gated diode has lower power density.

[0068] 3. More PN junction area is obtained compared to gated diode, so that the  
5 SOI non-gated diode has higher ESD robustness.

[0069] 4. The non-gated diode provided by the invention can be used in mixed voltage and analog/digital applications. In addition, the non-gated diode can be used as the input/output ESD protection circuit, and the protection circuit between Vss and Vdd under a forward biased condition.

10 [0070] Other embodiments of the invention will appear to those skilled in the art from consideration of the specification and practice of the invention disclosed herein. It is intended that the specification and examples to be considered as exemplary only, with a true scope and spirit of the invention being indicated by the following claims.